

In The Claims:

Please amend the claims as follows:

1. (Currently amended) An aqueous etching agent for anisotropically etching copper ~~in an etching process in an aqueous solution, the etching agent comprising consisting essentially of~~ potassium hydrogen peroxomonosulfate, having a concentration of said potassium hydrogen peroxomonosulfate falling within a range of about 0.08 to about 2.0 mol/l ~~10.01% to about 23.31% by weight of the etching agent,~~ and acetic acid, said etching agent etching the copper at an approximately uniform rate throughout the etching process, and wherein the acetic acid functions as a wetting agent.

2.-3. (Cancelled)

4. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film comprising an aqueous solution containing potassium hydrogen peroxomonosulfate and hydrofluoric acid.

5. (Withdrawn) An etching agent for a laminated film of a molybdenum film and a copper film comprising an aqueous solution containing potassium hydrogen peroxomonosulfate, phosphoric acid and nitric acid.

6. (Withdrawn) An etching agent for a laminated film of a chromium film and a copper film comprising an aqueous solution containing potassium hydrogen peroxomonosulfate and hydrochloric acid.

7. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film comprising an aqueous solution containing a peroxomonosulfate salt, hydrofluoric acid, and hydrochloric acid or a chloride.

8. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film comprising an aqueous solution containing a peroxosulfate salt and a fluoride.

9. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film according to Claim 7, wherein said peroxosulfate salt comprises any one or more compounds selected from KHSO_5 , NaHSO_5 , $\text{K}_2\text{S}_2\text{O}_8$, $\text{Na}_2\text{S}_2\text{O}_8$ and $(\text{NH}_4)_2\text{S}_2\text{O}_8$.

10. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film according to Claim 7, wherein said chloride comprises an alkali metal chloride or ammonium chloride.

11. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film according to Claim 8, wherein said peroxosulfate salt comprises any one or more compounds selected from KHSO_5 , NaHSO_5 , $\text{K}_2\text{S}_2\text{O}_8$, $\text{Na}_2\text{S}_2\text{O}_8$ and $(\text{NH}_4)_2\text{S}_2\text{O}_8$.

12. (Withdrawn) An etching agent for a laminated film of a titanium film and a copper film according to Claim 8, wherein said fluoride comprises an alkali metal fluoride or ammonium fluoride.

13.-16. (Cancelled)

17. (Currently amended) An etching agent according to claim 1, wherein said etching agent ~~is capable of selectively etching the~~ etches copper.

18. (Currently amended) An etching agent for anisotropically etching a copper layer having an overlying mask pattern in an etching process ~~consisting essentially of~~, the etching agent comprising an aqueous solution containing potassium hydrogen peroxomonosulfate, having a concentration of said potassium hydrogen peroxomonosulfate falling within a range of about 0.08 to about 2.0 mol/l ~~10.01% to about 23.31% by weight of the etching agent~~, said etching agent etching the copper layer at an approximately uniform rate throughout the etching process, such that edges of the copper layer are substantially continuous with corresponding edges of the mask pattern.

19. (Currently amended) An etching agent according to claim ~~47~~ 18, wherein said etching agent is capable of selectively etching the copper.

20. (New) An aqueous etching solution for anisotropically etching a copper layer having a mask pattern thereon, the solution comprising potassium hydrogen peroxomonosulfate and acetic acid, wherein the acetic acid continuously wets exposed surfaces of the copper layer and the potassium hydrogen peroxomonosulfate uniformly etches the copper layer, such that the copper layer is etched to substantially the same dimensions as the mask pattern.

21. (New) The aqueous etching solution of claim 20, wherein the solution comprises a potassium hydrogen peroxomonosulfate concentration of about 0.08 to about 2.0 mol/l.

22. (New) The aqueous etching solution of claim 21, wherein the solution comprises a weight ratio of acetic acid to potassium hydrogen peroxomonosulfate of about 10% to about 75%.

23. (New) The aqueous etching solution of claim 20, wherein the copper layer has a thickness of about 100nm to about 200nm.

24. (New) The aqueous etching solution of claim 20, wherein the solution etches the copper layer such that edges of the copper layer are substantially continuous with corresponding edges of the mask pattern.

25. (New) The aqueous etching solution of claim 20, wherein the copper layer is layer comprises a gate electrode.

26. (New) The aqueous etching solution of claim 20, wherein the copper layer is layer comprises a wiring layer.